

Rev.E Mar-2016

SOT-323

NPN

Silicon NPN transistor in

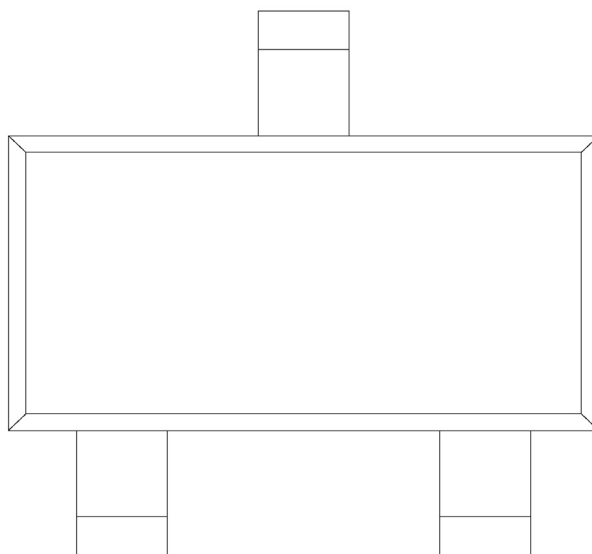


Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	40	V
Collector to Emitter Voltage	$V_{CEO}$	25	V
Emitter to Base Voltage	$V_{EBO}$	5.0	V
Collector Current - Continuous	$I_C$	50	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=50\mu A$	40			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=1.0mA$	25			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=50\mu A$	5.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=24V$			0.5	$\mu A$
Emitter Base Cut-Off Current	$I_{EBO}$	$V_{EB}=3.0V$			0.5	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=6.0V$ $I_C=1.0mA$	56		270	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA$ $I_B=1.0mA$		0.1	0.3	V
Transition Frequency	$f_T$	$V_{CE}=6.0V$ $f=100MHz$ $I_C=1.0mA$	150	300		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=6.0V$ $f=1.0MHz$ $I_E=0$		1.3	2.2	pF







H

A

N             $h_{FE}$

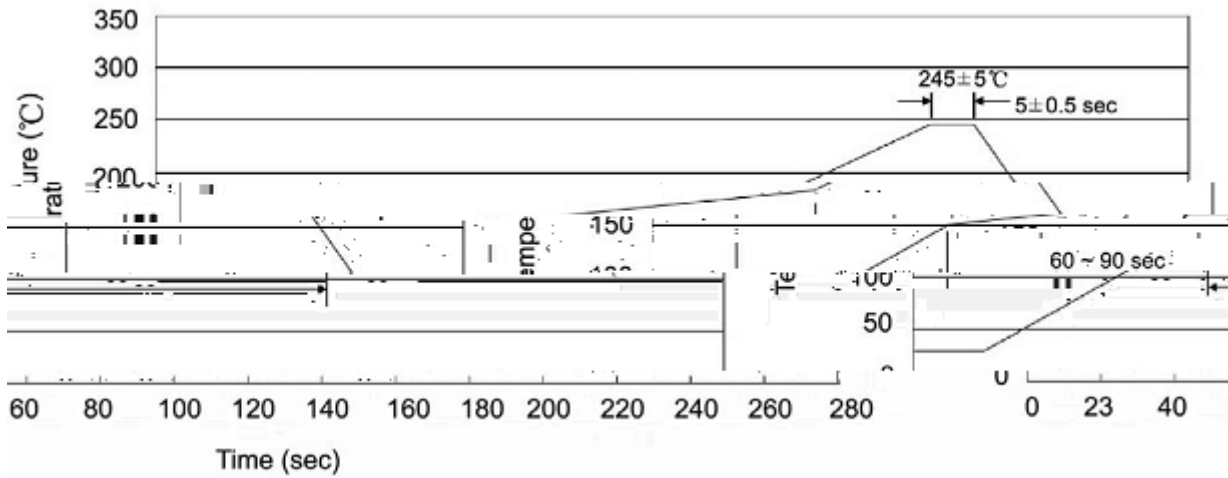
Note:

H:            Company Code.

A:            Product Type.

N             $h_{FE}$

## K\d g\iXk i\`Gif]`d`]fi`@`l`]\fn`Jfd`li`e`^ZGY\$=i\`z



Note:

- |   |       |     |    |           |   |
|---|-------|-----|----|-----------|---|
| 1 | 25    | 150 | 60 | 90sec;    | 1.Preheating:25~150 , Time:60~90sec.    |
| 2 | 245±5 |     |    | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 |       |     | 2  | 10 /sec.  | 3. Cooling Speed: 2~10 /sec.            |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205